

High Speed, Precision JFET Input Operational Amplifier

FEATURES

- **Guaranteed** Slew Rate: 23V/ μ s Min
- **Guaranteed** Offset Voltage: 250 μ V Max
–55°C to 125°C: 750 μ V Max
- **Guaranteed** Drift: 5 μ V/°C Max
- **Guaranteed** Bias Current:
70°C, 180pA Max
125°C, 4nA Max
- Gain-Bandwidth Product: 8.5MHz Typ
- Settling Time to 0.05% (10V Step): 0.9 μ s Typ

APPLICATIONS

- Fast D/A Output Amplifiers (12, 14, 16 Bits)
- High Speed Instrumentation
- Fast, Precision Sample and Hold
- Voltage-to-Frequency Converters
- Logarithmic Amplifiers

DESCRIPTION

The LT[®]1022 JFET input operational amplifier combines high speed and precision performance.


A 26V/ μ s slew rate and 8.5MHz gain-bandwidth product are simultaneously achieved with offset voltage of typically 80 μ V, 1.5 μ V/°C drift, bias currents of 50pA at 70°C, 500pA at 125°C. The output delivers 20mA of load current without gain degradation.

The 250 μ V maximum offset voltage specification represents less than 1/2 least significant bit error in a 14-bit, 10V system.

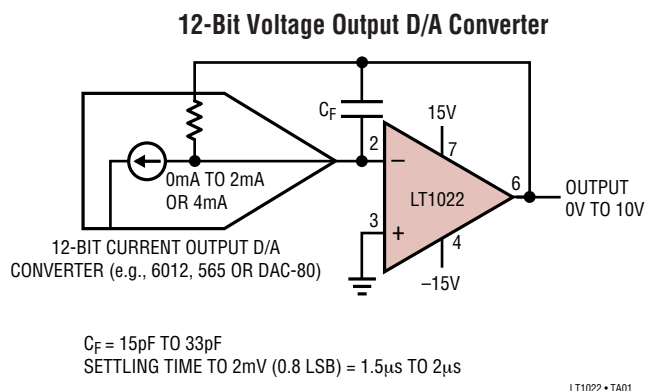
The LT1022A meets or exceeds all OP-16A and OP-16E specifications. It is faster and more accurate without stability problems at cold temperatures.

The LT1022 can be used as the output amplifier for 12-bit current output D/A converters, as shown below.

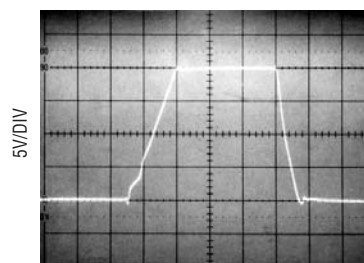
For a more accurate, lower power dissipation, but slower JFET input op amp, please refer to the LT1055 data sheet.

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TYPICAL APPLICATION



Large-Signal Response



$A_V = 1$
 $C_L = 100\text{pF}$
 $T_A = 25^\circ\text{C}$
 $V_S = \pm 15\text{V}$

LT1022

ABSOLUTE MAXIMUM RATINGS

(Note 1)

Supply Voltage	±20V
Differential Input Voltage	±40V
Input Voltage	±20V
Output Short Circuit Duration	Indefinite

Operating Temperature Range

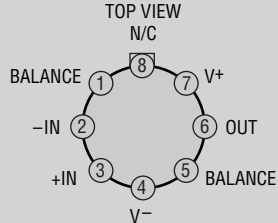
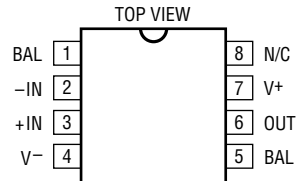
LT1022AM/1022M (**OBSOLETE**).....-55°C to 125°C

LT1022AC/1022C

Storage Temperature Range

Lead Temperature (Soldering, 10 sec.)..... 300°C

PACKAGE/ORDER INFORMATION

 <p>METAL CAN H PACKAGE T_{JMAX} = 150°C, θ_{JA} = 150°C/W, θ_{JC} = 45°C/W</p> <p>OBSOLETE PACKAGE Consider the N8 Package as an Alternate Source</p>	ORDER PART NUMBER	 <p>N8 PACKAGE 8-LEAD PDIP T_{JMAX} = 100°C, θ_{JA} = 130°C/W</p>	ORDER PART NUMBER
	LT1022AMH LT1022MH LT1022ACH LT1022CH		LT1022CN8

Consult LTC Marketing for parts specified with wider operating temperature ranges.

ELECTRICAL CHARACTERISTICS

V_S = ±15V, T_A = 25°C, V_{CM} = 0V unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	LT1022AM LT1022AC			LT1022M, LT1022CH LT1022CN8			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
V _{OS}	Input Offset Voltage (Note 2)	H Package N8 Package		80	250		100	600	μV μV
I _{OS}	Input Offset Current	Fully Warmed Up		2	10		2	20	pA
I _B	Input Bias Current	Fully Warmed Up V _{CM} = +10V		±10 30	±50 100		±10 30	±50 150	pA pA
	Input Resistance—Differential —Common Mode	V _{CM} = -11V to 8V V _{CM} = 8V to 11V		10 ¹² 10 ¹² 10 ¹¹			10 ¹² 10 ¹² 10 ¹¹		Ω Ω Ω
	Input Capacitance			4			4		pF
e _n	Input Noise Voltage	0.1Hz to 10Hz		2.5			2.8		μV/p-p
e _n	Input Noise Voltage Density	f ₀ = 10Hz (Note 3) f ₀ = 1kHz (Note 4)		28 14	50 20		30 15	60 22	nV/√Hz nV/√Hz
i _n	Input Noise Current Density	f ₀ = 10Hz, 1kHz (Note 5)		1.8	4		1.8	4	fA/√Hz
A _{VOL}	Large Signal Voltage Gain	V ₀ = ±10V R _L = 2k R _L = 1k	150 130	400 300		120 100	400 300		V/mV V/mV
	Input Voltage Range		±10.5	±12		±10.5	±12		V
CMRR	Common-Mode Rejection Ratio	V _{CM} = ±10.5V	86	94		82	92		dB
PSRR	Power Supply Rejection Ratio	V _S = ±10V to ±18V	88	104		86	102		dB
V _{OUT}	Output Voltage Swing	R _L = 2k	±12	±13.2		±12	±13.2		V
SR	Slew Rate		23	26		18	24		V/μs

1022fa

ELECTRICAL CHARACTERISTICS

$V_S = \pm 15V$, $T_A = 25^\circ C$, $V_{CM} = 0V$ unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	LT1022AM LT1022AC			LT1022M, LT1022CH LT1022CN8			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
GBW	Gain-Bandwidth Product	f = 1MHz	8.5			8.0			MHz
I_S	Supply Current		5.2	7.0		5.2	7.0		mA
	Settling Time	A = +1 or A = -1 10V Step to 0.05% 10V Step to 0.02%	0.9 1.3			0.9 1.3			μs μs
	Offset Voltage Adjustment Range	$R_{POT} = 100k$	± 7			± 7			mV

The ● denotes the specifications which apply over the full operating temperature range of $V_{CM} = 0V$, $0^\circ C \leq T_A \leq 70^\circ C$. $V_S = \pm 15V$, unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	LT1022AC			LT1022CH LT1022CN8			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OS}	Input Offset Voltage (Note 2)	H Package	●	140	480	180	1000	μV	
		N8 Package	●			300	1700	μV	
	Average Temperature Coefficient of Input Offset Voltage	H Package N8 Package (Note 6)	●	1.3	5.0	1.8	9.0	$\mu V/^\circ C$ $\mu V/^\circ C$	
I_{OS}	Input Offset Current	Warmed Up, $T_A = 70^\circ C$	●	15	80	18	100	pA	
I_B	Input Bias Current	Warmed Up, $T_A = 70^\circ C$	●	± 50	± 200	± 60	± 250	pA	
A_{VOL}	Large-Signal Voltage Gain	$V_O = \pm 10V$, $R_L = 2k$	●	80	250	60	250	V/mV	
CMRR	Common Mode Rejection Ratio	$V_{CM} = \pm 10.4V$	●	85	93	80	91	dB	
PSRR	Power Supply Rejection Ratio	$V_S = \pm 10V$ to $\pm 18V$	●	86	103	84	101	dB	
V_{OUT}	Output Voltage Swing	$R_L = 2k$	●	± 12	± 13.1	± 12	± 13.1	V	

The ● denotes the specifications which apply over the full operating temperature range of $-55^\circ C \leq T_A \leq 125^\circ C$. $V_S = \pm 15V$, $V_{CM} = 0V$, unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	LT1022AM			LT1022M			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OS}	Input Offset Voltage	(Note 2)	●	230	750	300	1500	μV	
		(Note 6)	●	1.5	5.0	2.0	9.0	$\mu V/^\circ C$	
I_{OS}	Input Offset Current	Warmed Up, $T_A = 125^\circ C$	●	0.3	2.0	0.30	3.0	nA	
I_B	Input Bias Current	Warmed Up, $T_A = 125^\circ C$	●	± 0.5	± 4.0	± 0.7	± 6.0	nA	
A_{VOL}	Large Signal Voltage Gain	$V_O = \pm 10V$, $R_L = 2k$	●	40	120	35	120	V/mV	
CMRR	Common-Mode Rejection Ratio	$V_{CM} = \pm 10.4V$	●	85	92	80	90	dB	
PSRR	Power Supply Rejection Ratio	$V_S = \pm 10V$ to $\pm 17V$	●	86	102	84	100	dB	
V_{OUT}	Output Voltage Swing	$R_L = 2k$	●	± 12	± 12.9	± 12	± 12.9	V	

Note 1: Absolute Maximum Ratings are those values beyond which the life of a device may be impaired.

Note 2: Offset voltage is measured under two different conditions:
 (a) approximately 0.5 seconds after application of power;
 (b) at $T_A = 25^\circ C$, with the chip self-heated to approximately $45^\circ C$ to account for chip temperature rise when the device is fully warmed up.

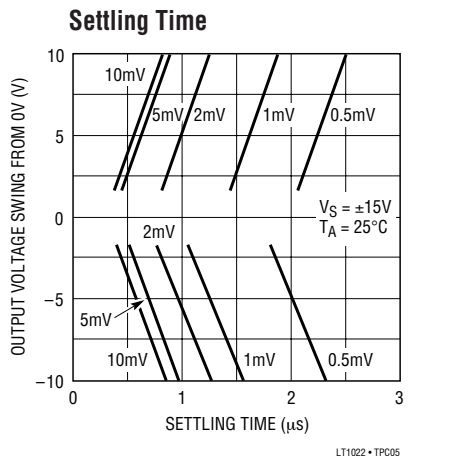
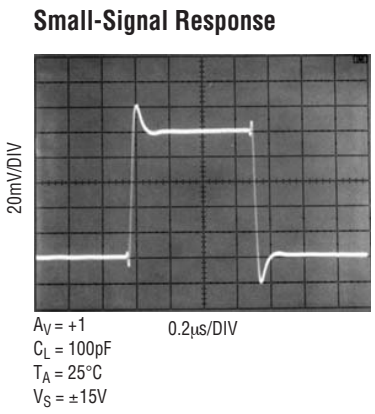
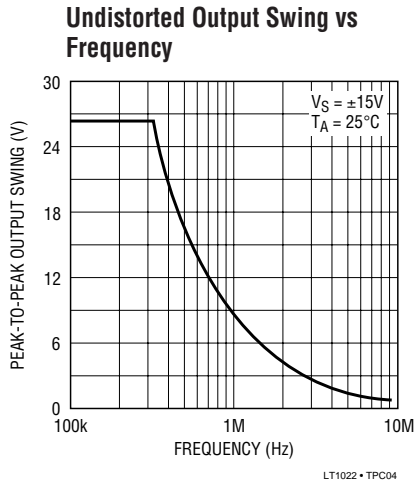
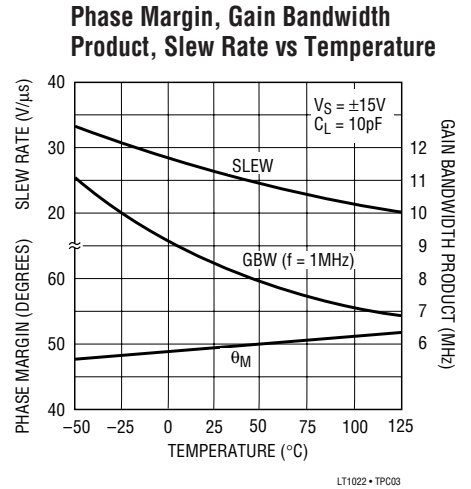
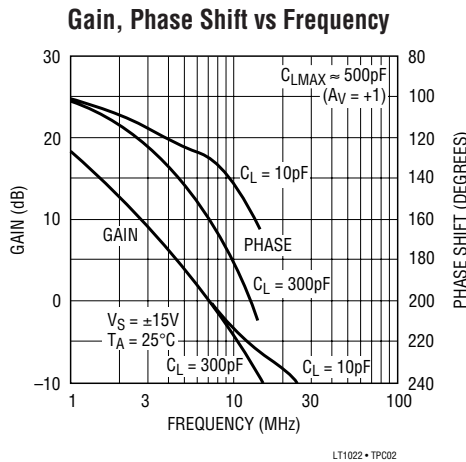
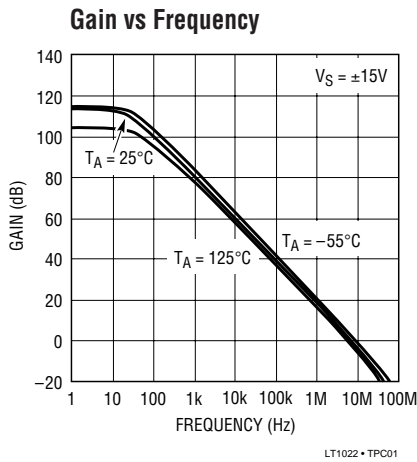
Note 3: 10Hz noise voltage density is sample tested on every lot of A grades. Devices 100% tested at 10Hz are available on request.

Note 4: This parameter is tested on a sample basis only.

Note 5: Current noise is calculated from the formula: $i_n = (2qI_B)^{1/2}$, where $q = 1.6 \cdot 10^{-19}$ coulomb. The noise of source resistors up to $1G\Omega$ swamps the contribution of current noise.

Note 6: Offset voltage drift with temperature is practically unchanged when the offset voltage is trimmed to zero with a 100k potentiometer between the balance terminals and the wiper tied to V^+ . Devices tested to tighter drift specifications are available on request.

TYPICAL PERFORMANCE CHARACTERISTICS



The typical behavior of many LT1022 parameters is identical to the LT1056. Please refer to the LT1055/1056 data sheet for the following typical performance characteristics:

- Input Bias and Offset Currents vs Temperature
- Input Bias Current Over the Common-Mode Range
- Distribution of Input Offset Voltage (H and N8 Package)
- Distribution of Offset Voltage Drift with Temperature
- Warm-Up Drift
- Long Term Drift of Representative Units
- 0.1Hz to 10Hz Noise
- Voltage Noise vs Frequency
- Noise vs Chip Temperature

- Short Circuit Current vs Time
- Output Impedance vs Frequency
- Common Mode Range vs Temperature
- Common Mode and Power Supply Rejections vs Temperature
- Common Mode Rejection Ratio vs Frequency
- Power Supply Rejection Ratio vs Frequency
- Voltage Gain vs Temperature
- Supply Current vs Supply Voltage
- Output Swing vs Load Resistance

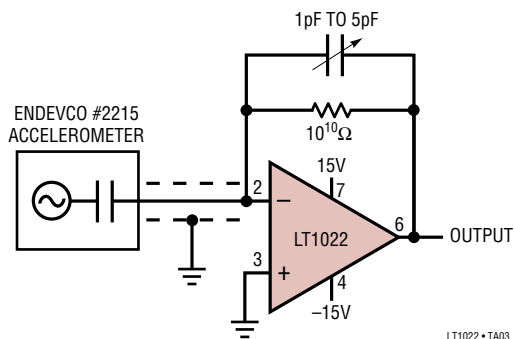
APPLICATIONS INFORMATION

The LT1056 applications information is directly applicable to the LT1022. Please consult the LT1055/1056 data sheet for details on:

- (1) plug-in compatibility to industry standard devices
- (2) offset nulling
- (3) achieving picoampere/microvolt performance
- (4) phase-reversal protection
- (5) high speed operation (including settling time test circuit)
- (6) noise performance
- (7) simplified circuit schematic

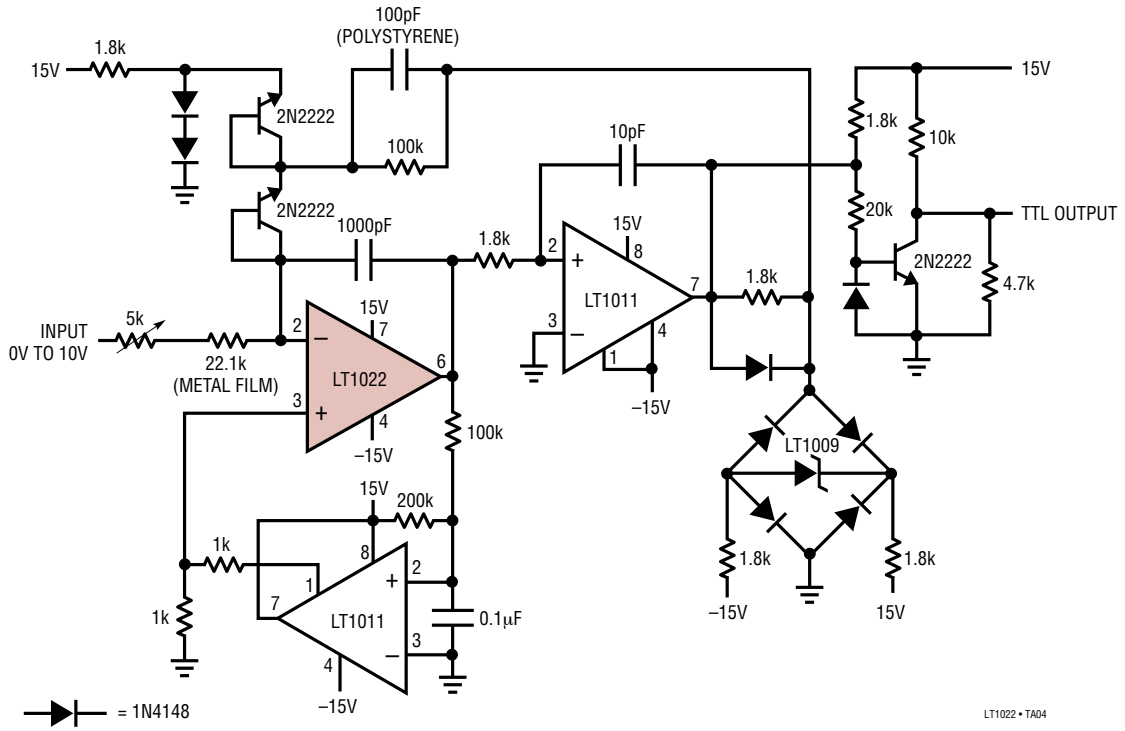
TYPICAL APPLICATIONS

Fast Piezoelectric Accelerometer



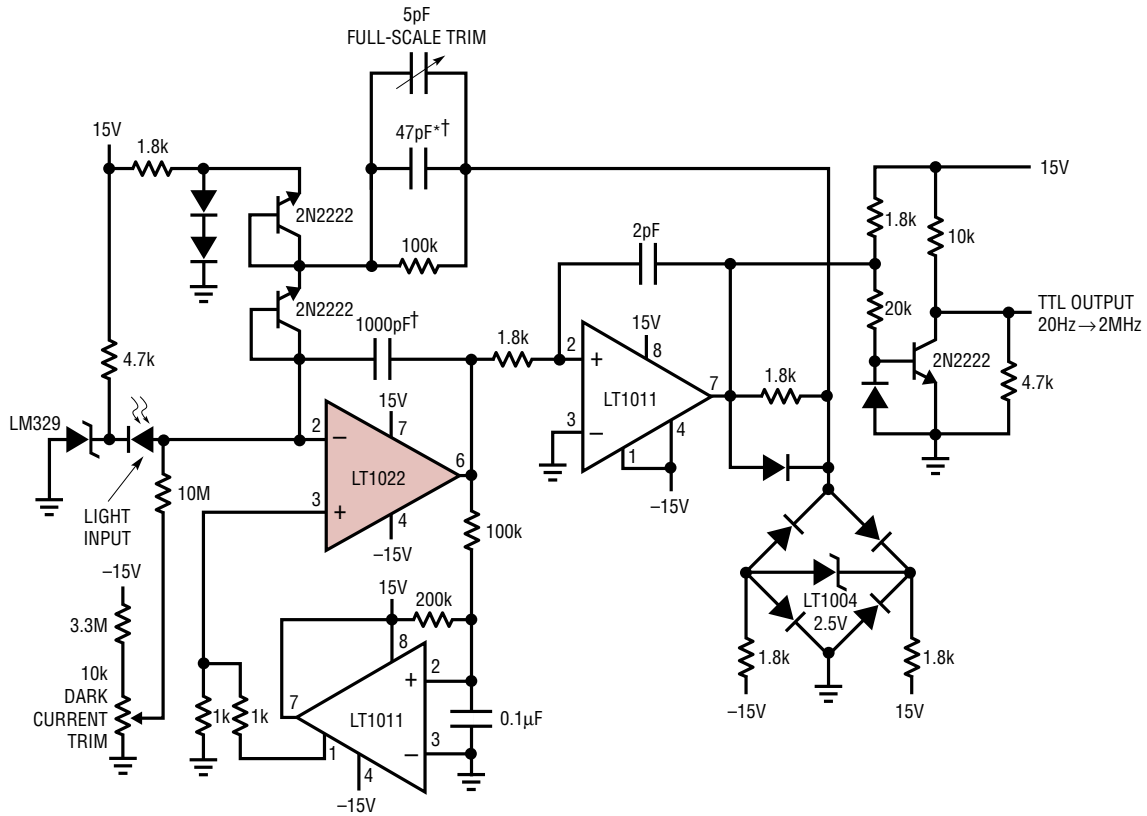
TYPICAL APPLICATIONS

10Hz to 1MHz Voltage-to-Frequency Converter



TYPICAL APPLICATIONS

PIN Photodiode-to-Frequency Converter



SCALE FACTOR =
1nW/Hz AT 900 NANOMETERS FROM 20nW TO 2mW

= HEWLETT PACKARD PHOTODIODE HP5082-4204

= 1N4148

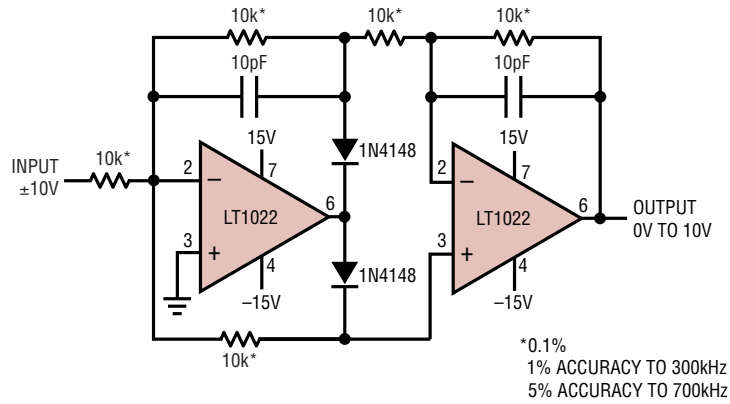
† POLYSTYRENE

* SELECT VALUE FOR 2mW IN = 2MHz OUT

LT1022 • TA05

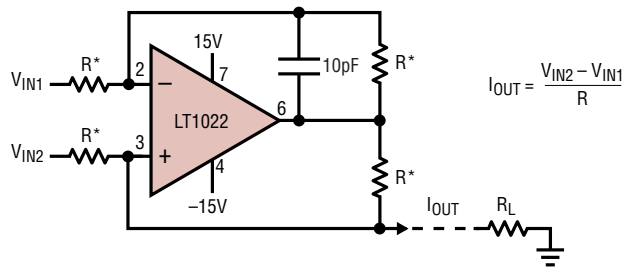
TYPICAL APPLICATIONS

Wide Bandwidth Absolute Value Circuit



LT1022 • TA06

Fast, Differential Input Current Source

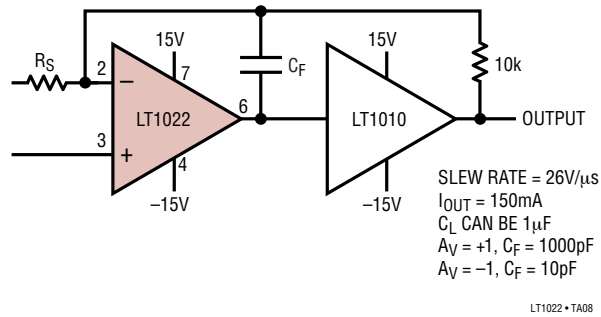


*MATCH TO 0.01%
FULL-SCALE POWER BANDWIDTH
= 1MHz FOR $I_{OUT}R = 8V_{P-P}$
= 400kHz FOR $I_{OUT}R = 20V_{P-P}$
MAXIMUM $I_{OUT} = 10mA_{P-P}$
COMMON-MODE VOLTAGE AT LT1022 INPUT = $\frac{I_{OUT}R \cdot R_L}{2}$

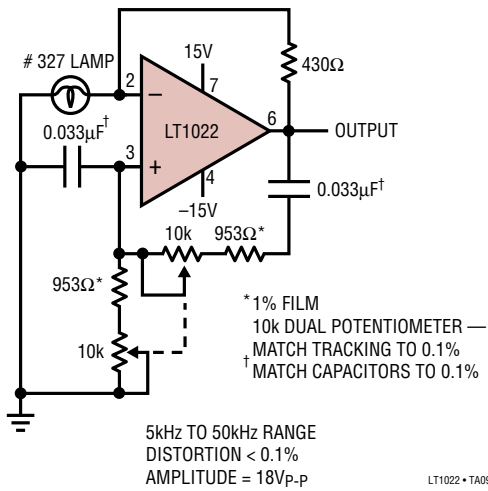
LT1022 • TA07

TYPICAL APPLICATIONS

High Output Current Op Amp

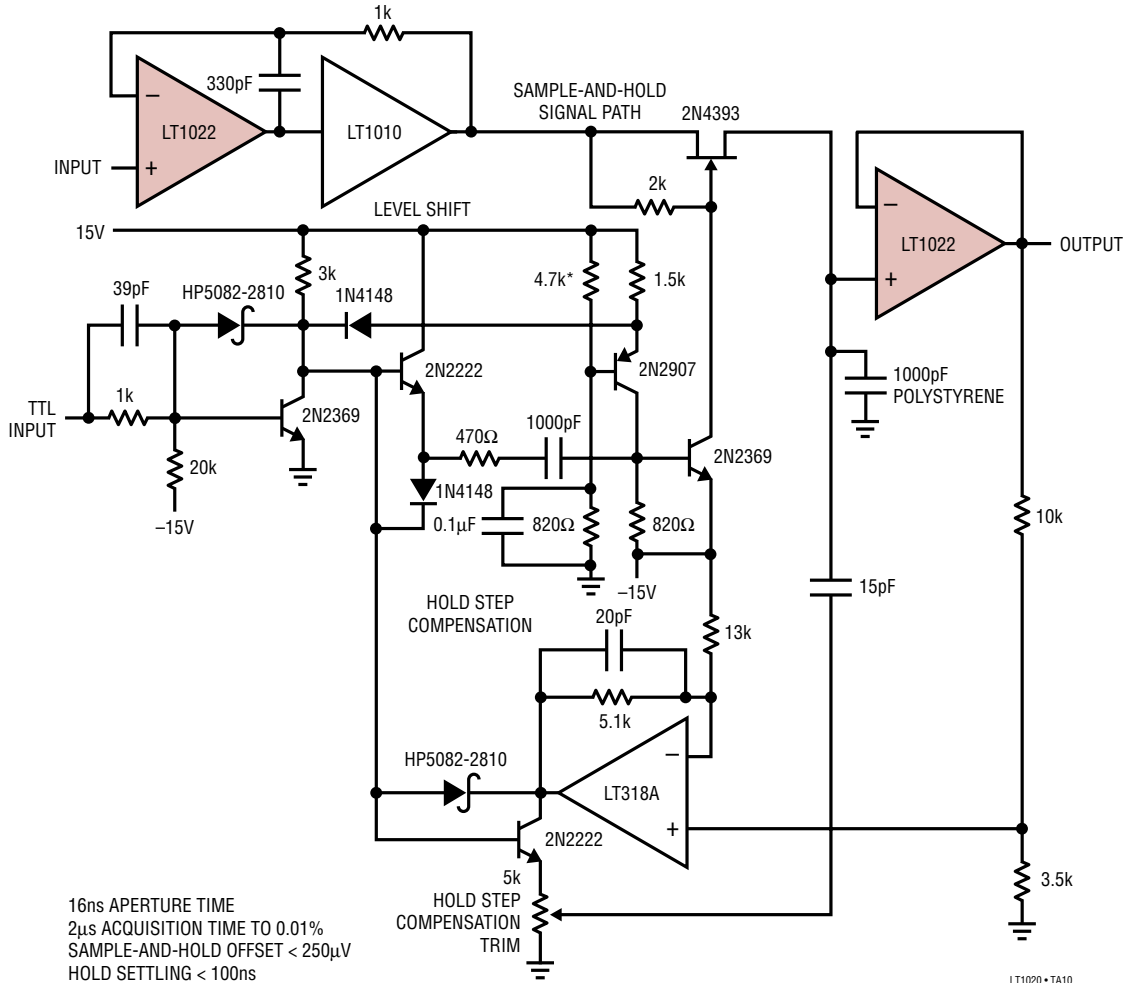


Low Distortion Sine Wave Oscillator



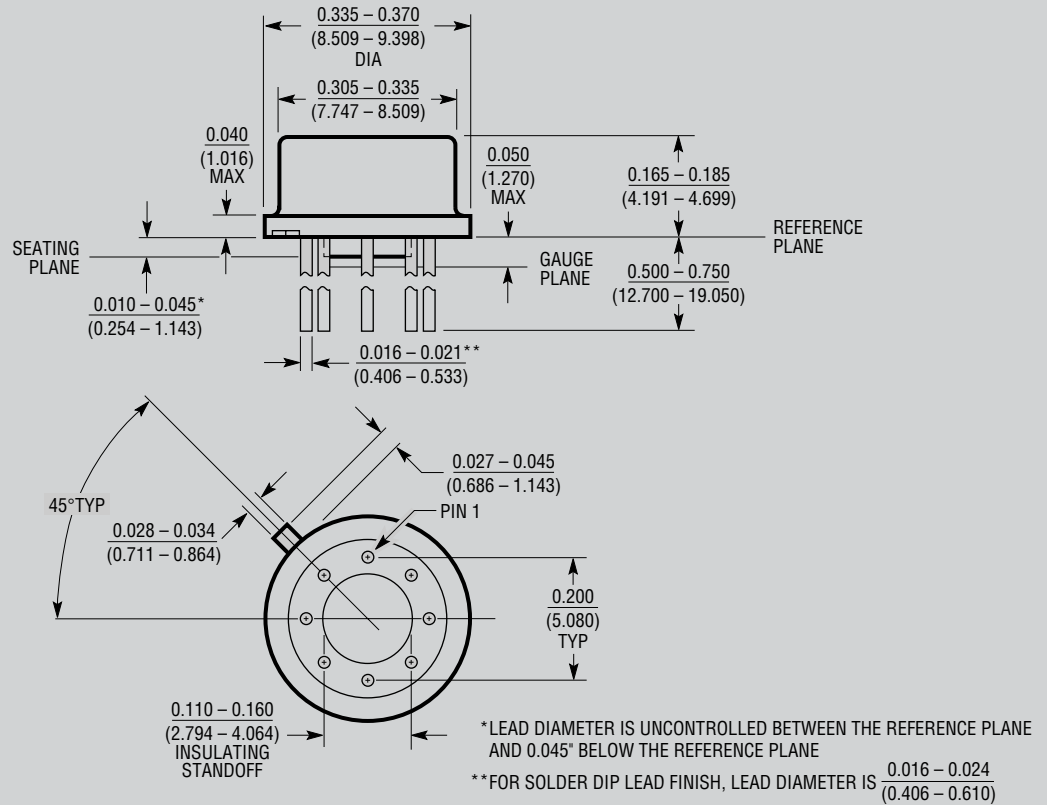
TYPICAL APPLICATIONS

Fast, Precision Sample-And-Hold



PACKAGE DESCRIPTION

H Package
8-Lead TO-5 Metal Can (.200 Inch PCD)
 (Reference LTC DWG # 05-08-1320)

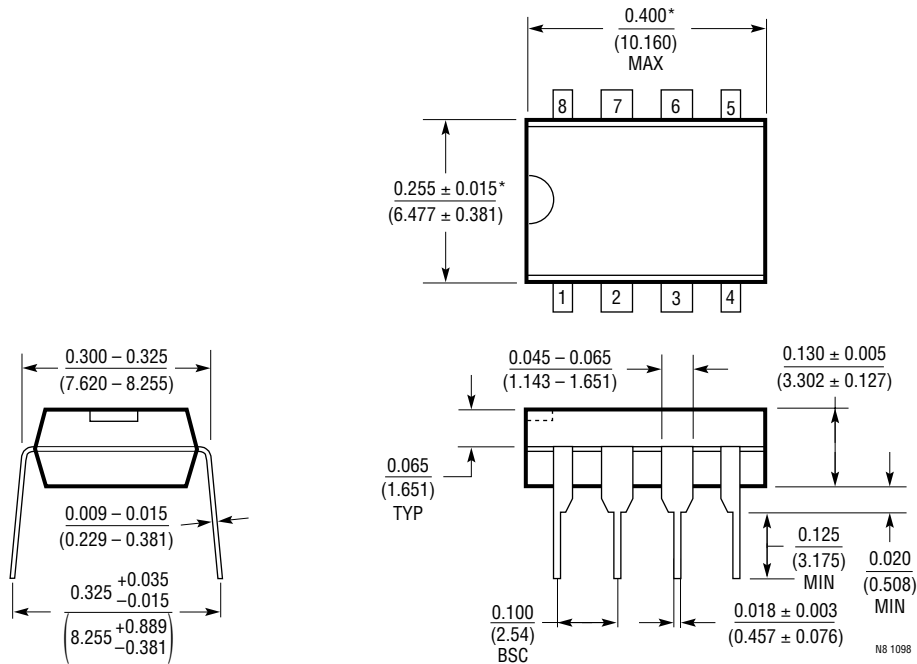


H8(TO-5) 0.200 PCD 1197

OBSOLETE PACKAGE

PACKAGE DESCRIPTION

N8 Package
8-Lead PDIP (Narrow .300 Inch)
 (Reference LTC DWG # 05-08-1510)



*THESE DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.
 MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.010 INCH (0.254mm)